



FDMA008P20LZ

Single P-Channel PowerTrench[®] MOSFET -20 V, -2.5 A, 13 mΩ

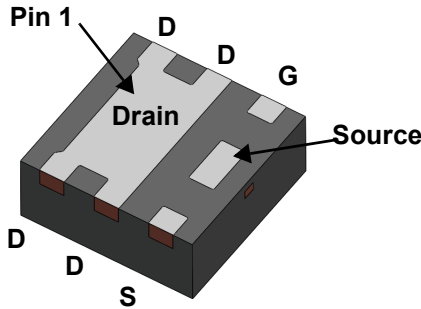
Features

- Max $r_{DS(on)}$ = 13 mΩ at $V_{GS} = -4.5$ V, $I_D = -2.5$ A
- Max $r_{DS(on)}$ = 16 mΩ at $V_{GS} = -2.5$ V, $I_D = -1.4$ A
- Max $r_{DS(on)}$ = 20 mΩ at $V_{GS} = -1.8$ V, $I_D = -1.0$ A
- Max $r_{DS(on)}$ = 30 mΩ at $V_{GS} = -1.5$ V, $I_D = -0.85$ A
- Low Profile - 0.8 mm maximum in the new package MicroFET 2x2 mm
- HBM ESD protection level > 1k V typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

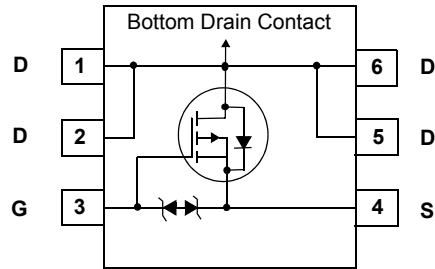


General Description

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance and zener diode protection against ESD. The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.



MicroFET 2X2 (Bottom View)



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	-2.5
	-Pulsed	(Note 5)	-164
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	54
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.4
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1b)	0.9
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMA008P20LZ	FDMA008P20LZ	MicroFET 2X2	7"	8 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-16		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0\text{ V}$			± 1	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\text{ }\mu\text{A}$	-0.4	-0.65	-1.4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -4.5\text{ V}$, $I_D = -2.5\text{ A}$		10	13	m Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -1.4\text{ A}$		12	16	
		$V_{GS} = -1.8\text{ V}$, $I_D = -1.0\text{ A}$		15	20	
		$V_{GS} = -1.5\text{ V}$, $I_D = -0.85\text{ A}$		20	30	
		$V_{GS} = -4.5\text{ V}$, $I_D = -2.5\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		12.8		
g_{FS}	Forward Transconductance	$V_{DD} = -5\text{ V}$, $I_D = -2.5\text{ A}$		26		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		3131	4383	pF
C_{oss}	Output Capacitance			424	594	pF
C_{rss}	Reverse Transfer Capacitance			386	540	pF
R_g	Gate Resistance			13	25	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -2.5\text{ A}$, $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		12	21	ns
t_r	Rise Time			17	30	ns
$t_{d(off)}$	Turn-Off Delay Time			239	382	ns
t_f	Fall Time			96	153	ns
Q_g	Total Gate Charge	$V_{GS} = -4.5\text{ V}$, $V_{DD} = -10\text{ V}$, $I_D = -2.5\text{ A}$		28	39	nC
Q_{gs}	Gate to Source Charge			3.6		nC
Q_{gd}	Gate to Drain "Miller" Charge			6.2		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -2\text{ A}$ (Note 2)		-0.6	-1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = -2.5\text{ A}$ (Note 2)		-0.8	-1.3	V
t_{rr}	Reverse Recovery Time	$I_F = -2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		28	46	ns
Q_{rr}	Reverse Recovery Charge			10	17	nC

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a. $52\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b. $145\text{ }^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width $< 300\text{ }\mu\text{s}$, Duty cycle $< 2.0\%$.
- The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.
- E_{AS} of 54 mJ is based on starting $T_J = 25\text{ }^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 20\text{ V}$, $V_{GS} = 4.5\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 19\text{ A}$.
- Pulsed I_d please refer to Fig.10 SOA curve for more details.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

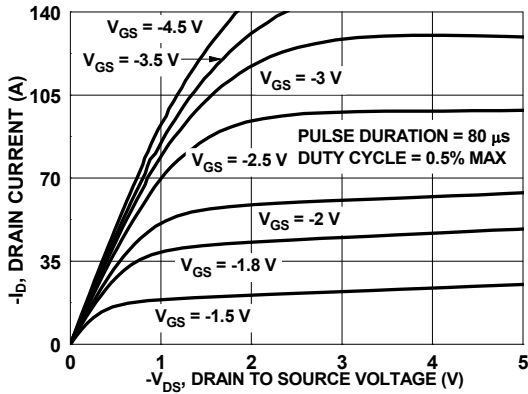


Figure 1. On-Region Characteristics

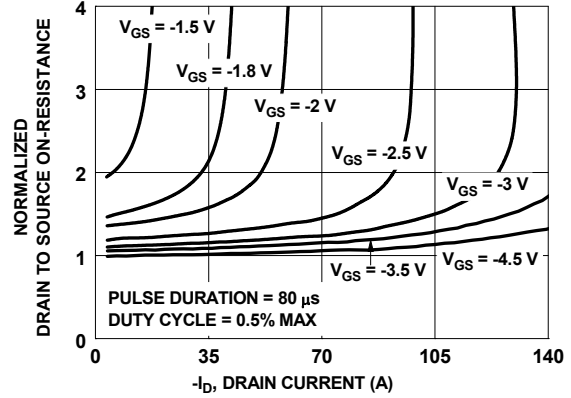


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

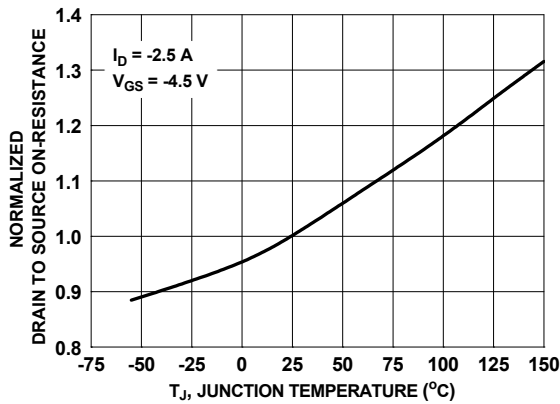


Figure 3. Normalized On-Resistance vs Junction Temperature

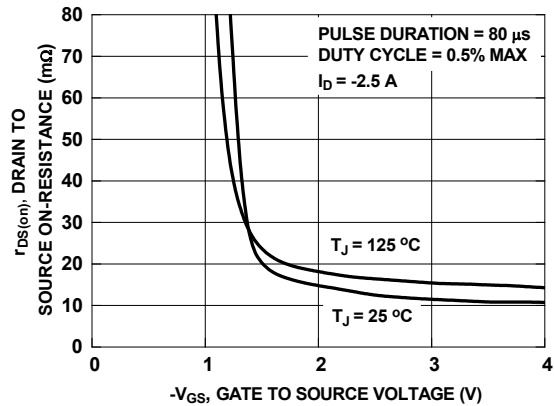


Figure 4. On-Resistance vs Gate to Source Voltage

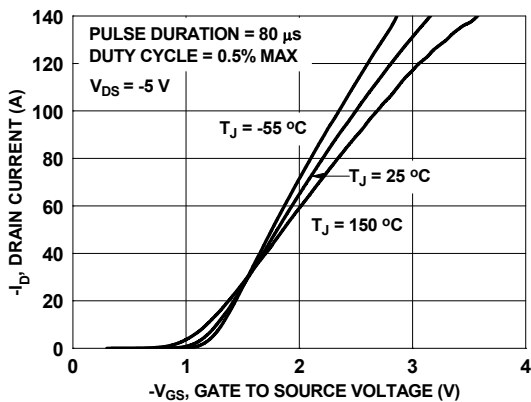


Figure 5. Transfer Characteristics

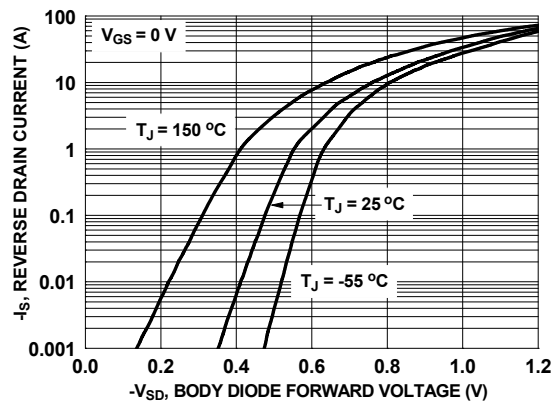


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

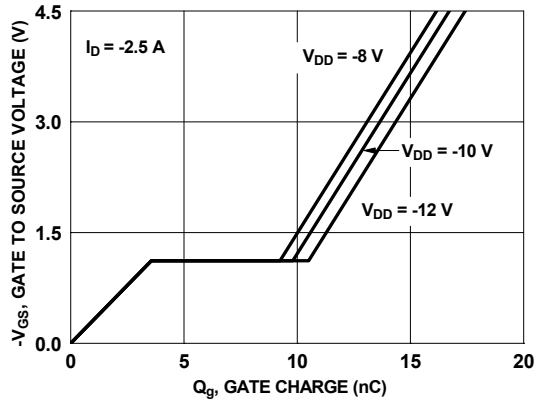


Figure 7. Gate Charge Characteristics

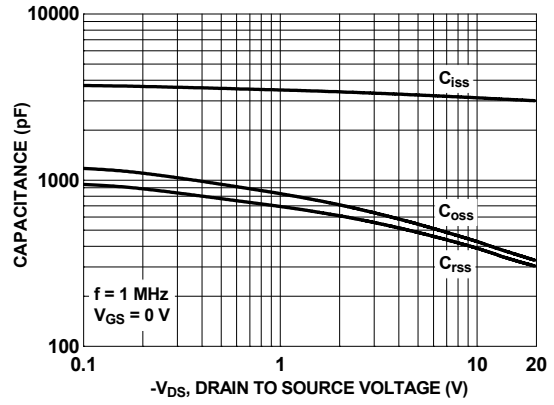


Figure 8. Capacitance vs Drain to Source Voltage

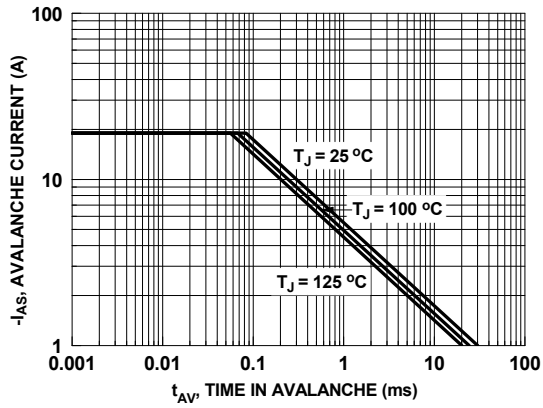


Figure 9. Unclamped Inductive Switching Capability

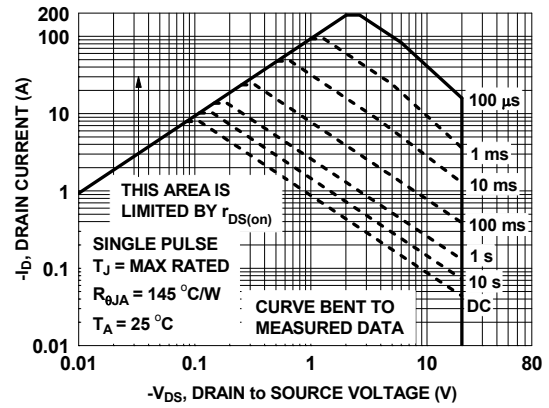


Figure 10. Forward Bias Safe Operating Area

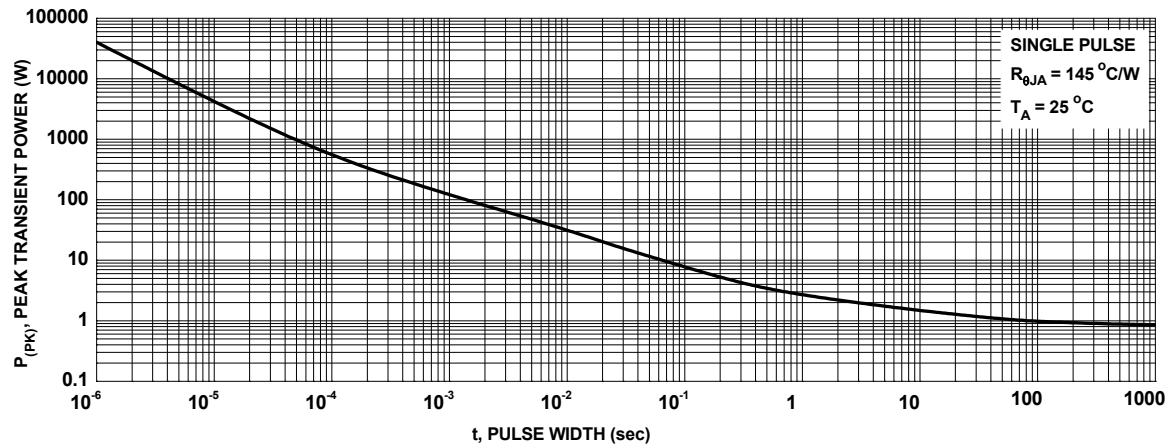


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

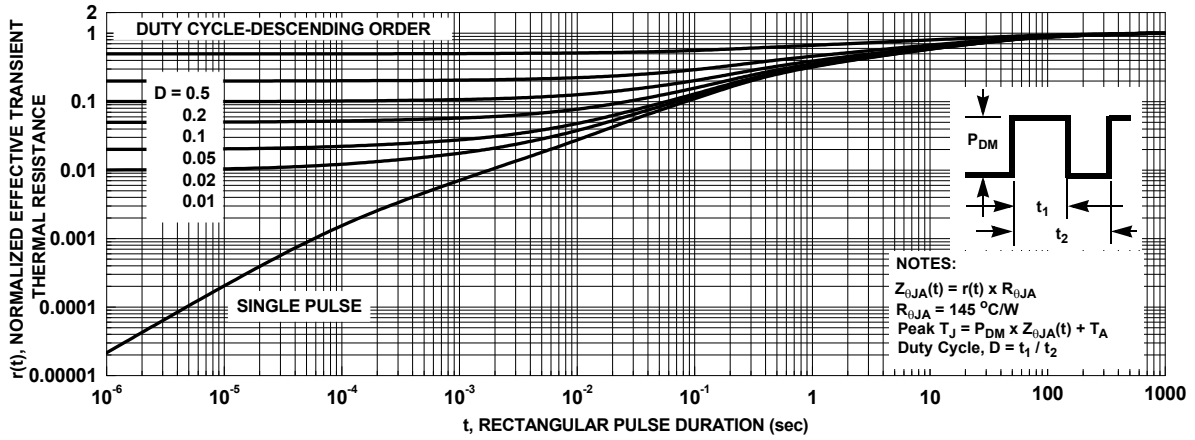


Figure 12. Junction-to-Ambient Transient Thermal Response Curve